

φ80 μm IR Pin-Point LED Chip OPA8508PPSA

1. Product Name

φ80 μm IR Pin-Point LED Chip OPA8508PPSA

2. Absolute Maximum Ratings

Ta=25°C

Parameter	Symbol	Rating	Unit
Power Dissipation	PD	170	mW
Forward Current	IF	80	mA
Reverse Voltage	VR	3	V
Operating Temperature	Topr	-30~+125	°C
Storage Temperature	Tstg	-40~+125	°C

3. Electro-Optical Characteristics

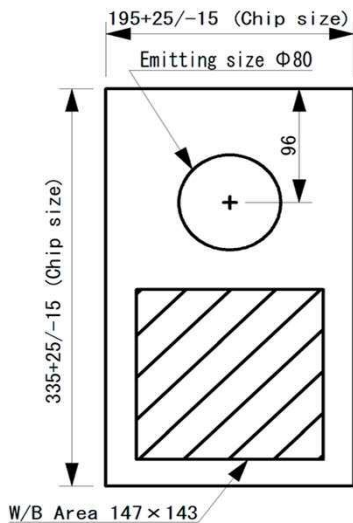
Ta=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=20mA	-	1.7	2.2	V
Reverse Current	IR	VR=3V	-	-	1.0	μA
Radiated Power※	Po	IF=20mA	0.80	1.10	-	mW
Peak Wavelength	λp	IF=20mA	-	850	-	nm

※ LED chip is mounted on TO-18 stem without resin coated.

Radiated Power is all light quantity that measured in integrating sphere owned by us.

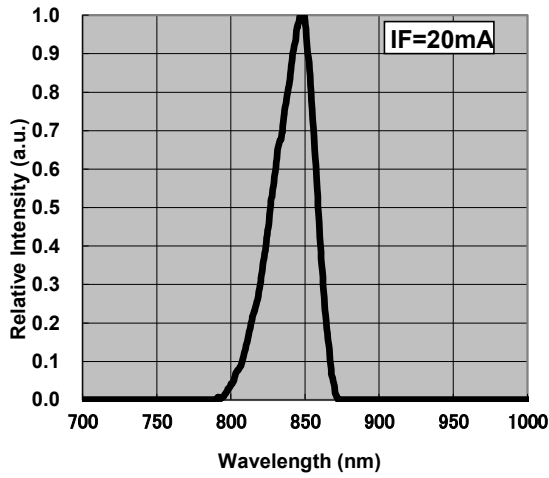
4. Dimension (Unit: μm)



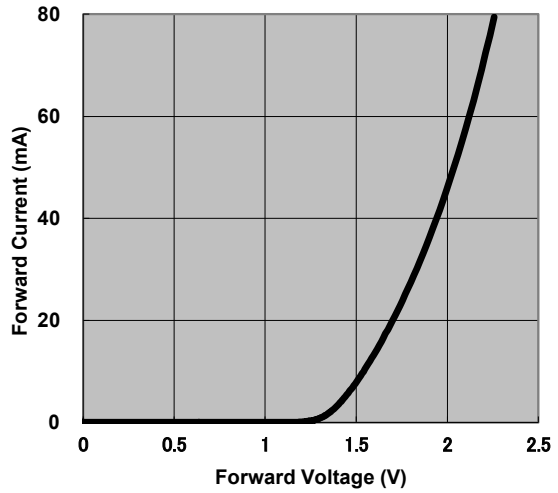
Material	AlGaAs/GaAs sub.
Emitting Surface	P Side
Surface Electrode	Au
Back Electrode	Au Alloy
Thickness	250±15 μm

The contents of this data sheet are subject to change without advance notice for the purpose of improvement. When using this product, would you please refer to the latest specifications.

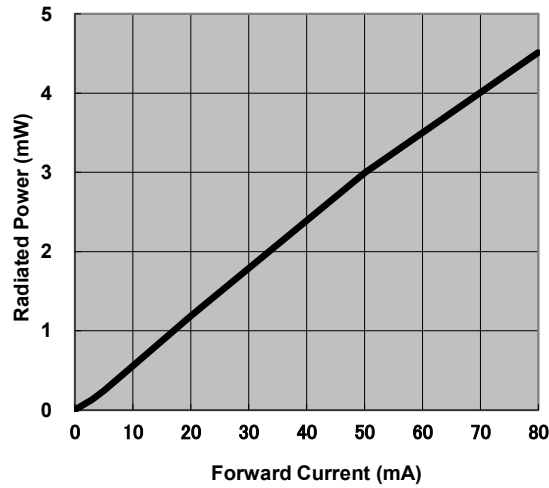
Emission Spectrum



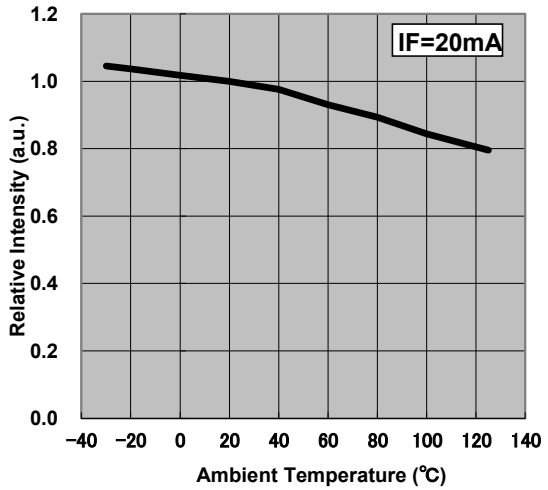
Forward Voltage vs. Forward Current



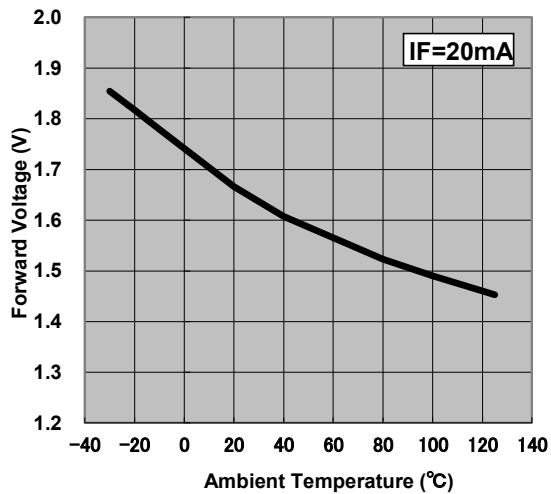
Forward Current vs. Radiated Power



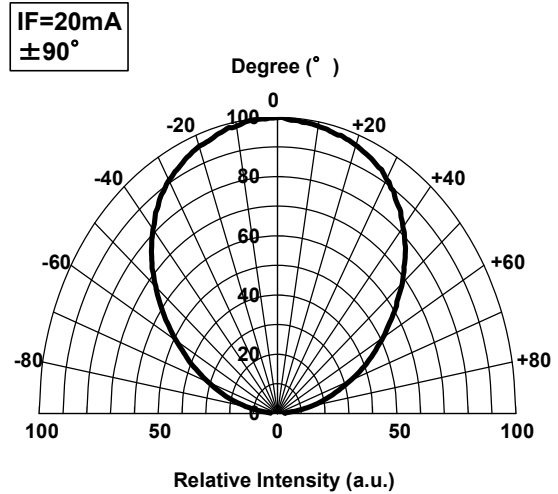
Ambient Temperature vs. Radiated Power



Ambient Temperature vs. Forward Voltage



Directivity



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